

/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

P_C, I_C , 8550

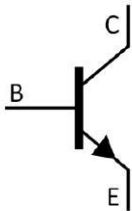
High P_C and I_C , complementary pair with 8550.

/ Applications

2W

2W output amplifier of portable radios in class B push-pull operation.

/ Equivalent Circuit



/ Pinning



PIN1 Collector PIN 2 Base PIN 3 Emitter

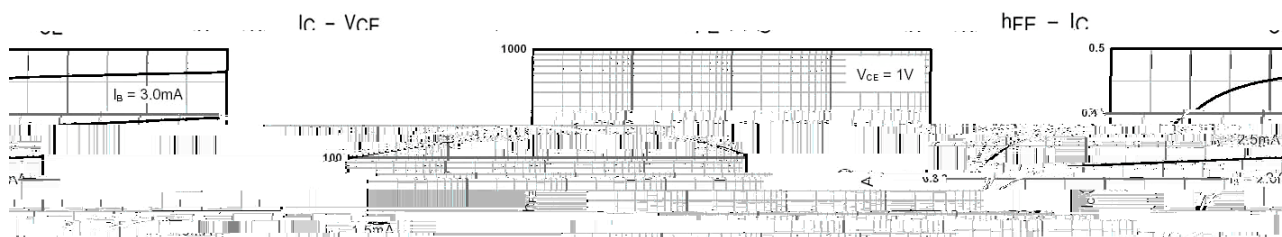
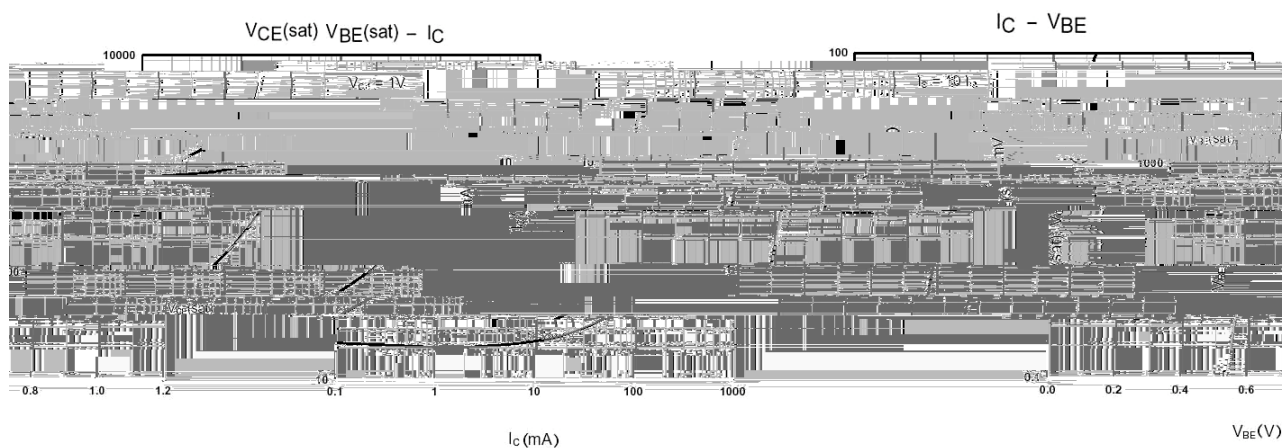
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	85~160	120~200	160~300

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	1.5	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$				

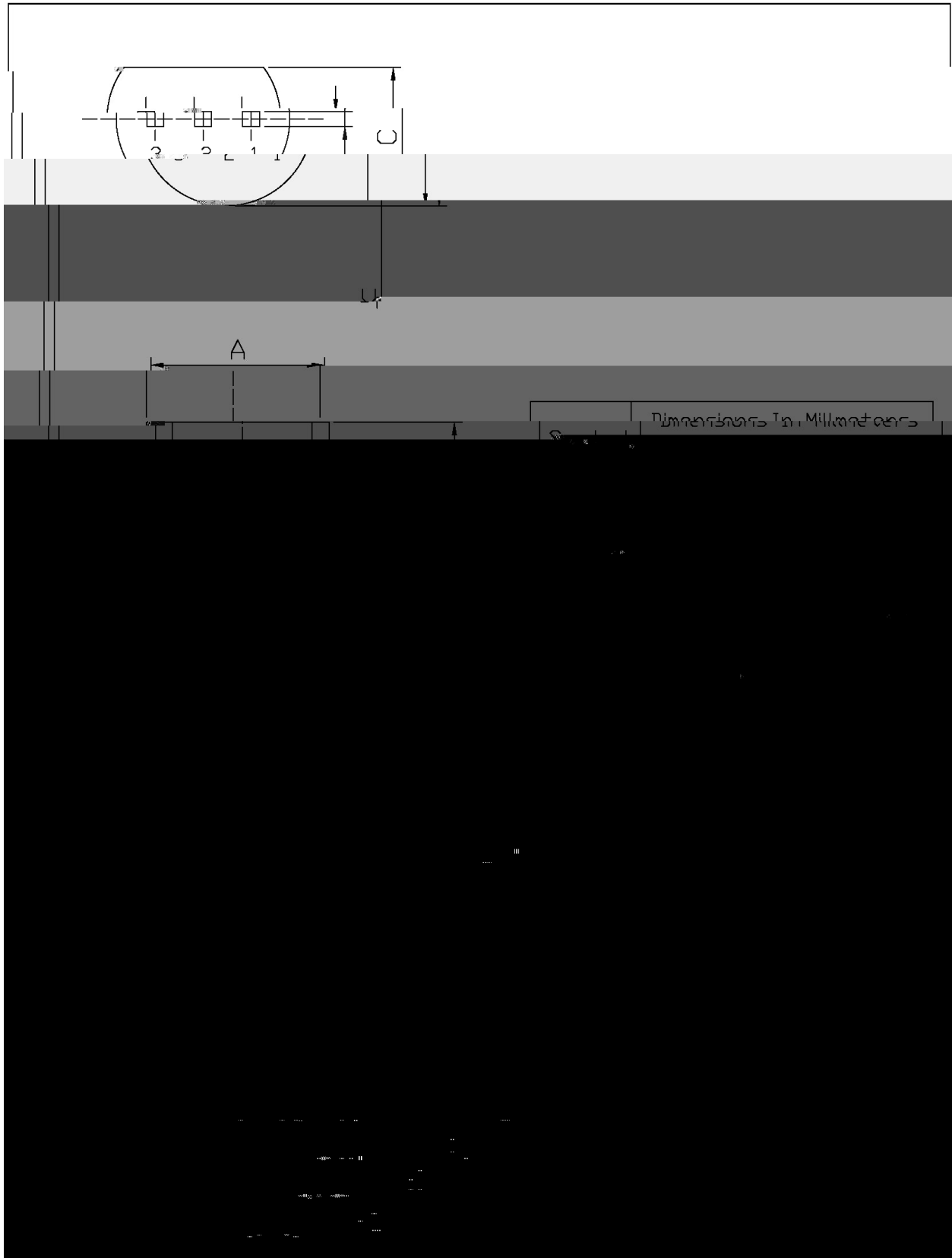
/ Electrical Characteristic Curve



/ Package Dimensions

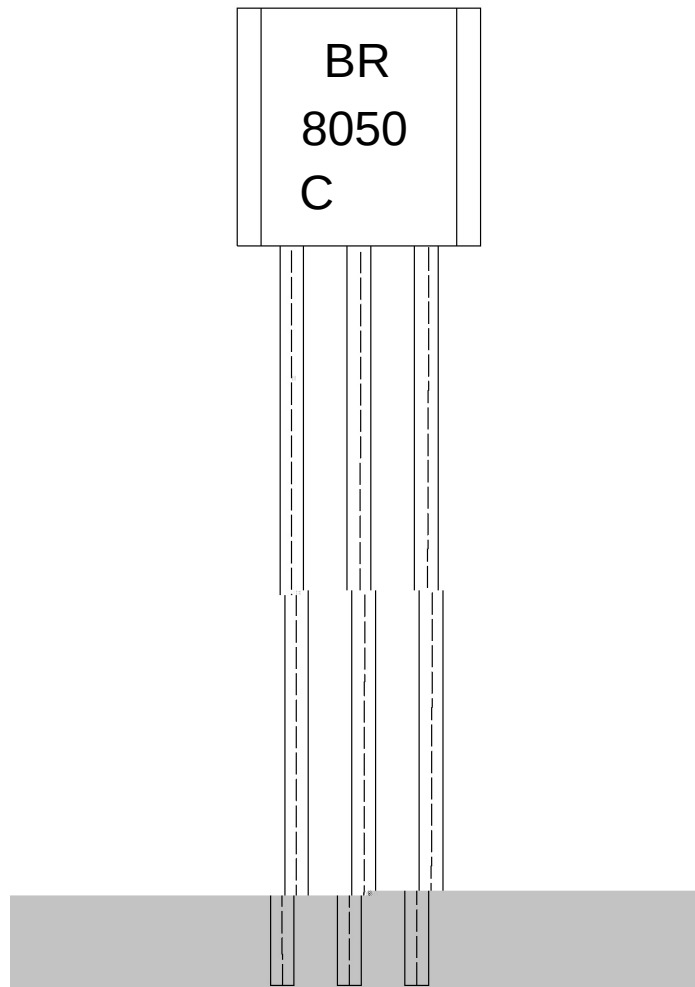
T0-92

Unit: mm





/ Marking Instructions



BR

8050

C: h_{FE}

Note:

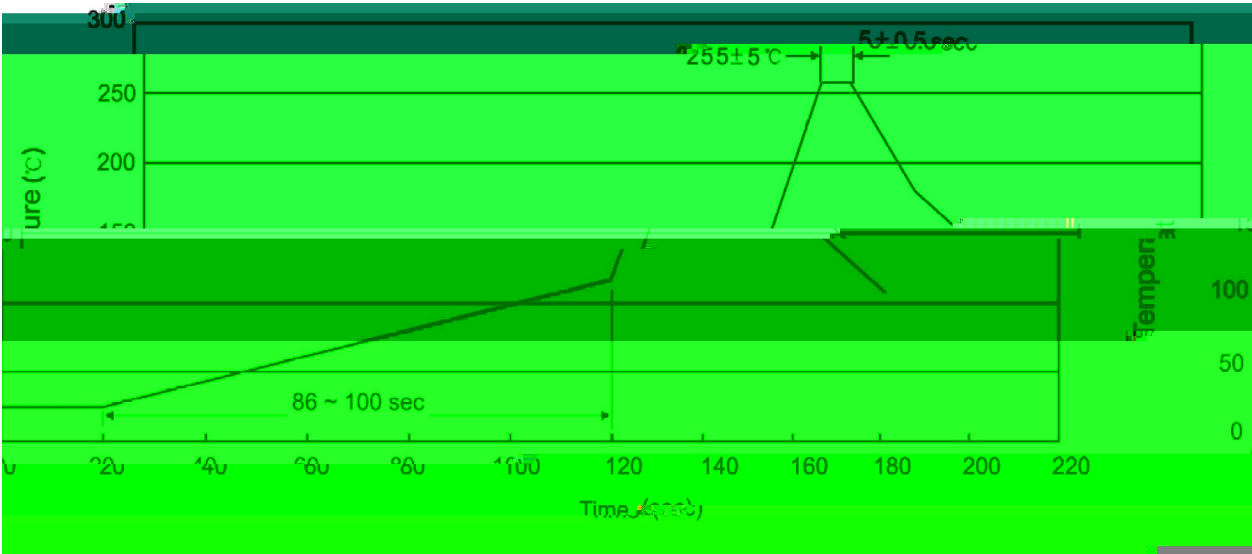
BR: Company Code.

8050: Product Type.

C: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK